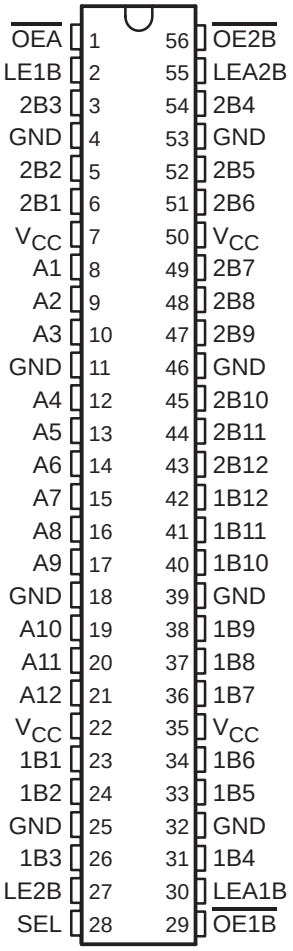
- **State-of-the-Art Advanced BiCMOS Technology (ABT) *Widebus*™ Design for 2.5-V and 3.3-V Operation and Low Static-Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 2.3-V to 3.6-V V_{CC})**
- **Typical V_{OLP} (Output Ground Bounce) <0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **High-Drive (–24 mA/24 mA at 2.5-V and –32/64mA at 3.3-V V_{CC})**
- **I_{off} and Power-Up 3-State Support Hot Insertion**
- **Use Bus Hold on Data Inputs in Place of External Pullup/Pulldown Resistors to Prevent the Bus From Floating**
- **Auto3-State Eliminates Bus Current Loading When Output Exceeds V_{CC} + 0.5 V**
- **Flow-Through Architecture Facilitates Printed Circuit Board Layout**
- **Distributed V_{CC} and GND Pins Minimize High-Speed Switching Noise**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV) Packages, and 380-mil Fine-Pitch Ceramic Flat (WD) Package**

NOTE: For tape and reel order entry:
The DGGR package is abbreviated to GR, and
the DGVR package is abbreviated to VR.

SN54ALVTH16260 . . . WD PACKAGE
SN74ALVTH16260 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The ’ALVTH16260 devices are 12-bit to 24-bit multiplexed D-type latches designed for 2.5-V or 3.3-V V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output-enable ($\overline{OE1B}$, $\overline{OE2B}$, and $\overline{OEA}$) inputs control the bus transceiver functions. The $\overline{OE1B}$ and $\overline{OE2B}$ control signals also allow bank control in the A-to-B direction.

description (continued)

The 'ALVTH16260 devices are used in applications where two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. Typical applications include multiplexing and/or demultiplexing address and data information in microprocessor or bus-interface applications. This device also is useful in memory-interleaving applications.

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

These devices are fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

When V_{CC} is between 0 and 1.2 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.2 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54ALVTH16260 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ALVTH16260 is characterized for operation from –40°C to 85°C.

Function Tables

B TO A ($\overline{OEB}$ = H)

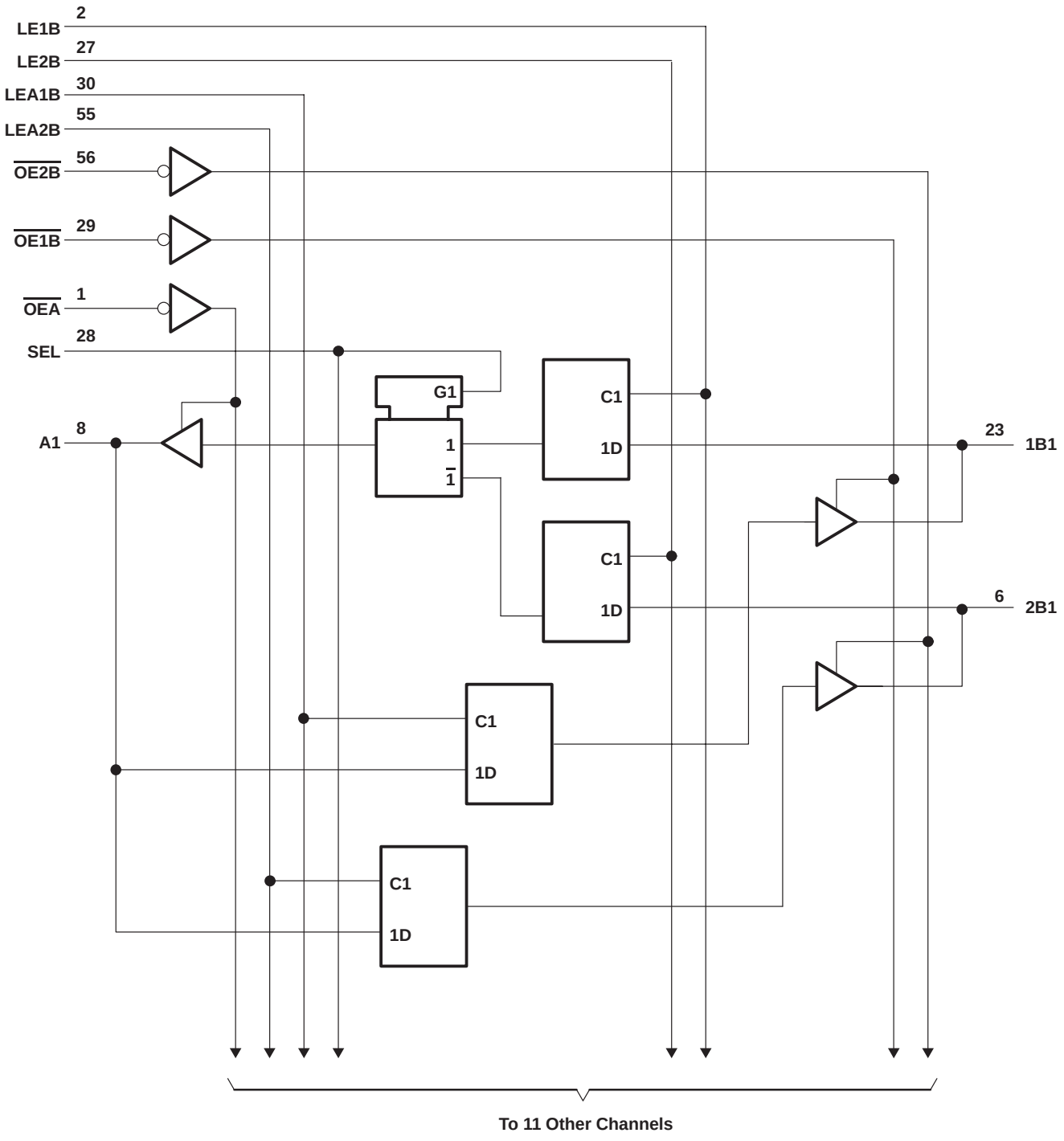
INPUTS						OUTPUT
1B	2B	SEL	LE1B	LE2B	$\overline{OEA}$	A
H	X	H	H	X	L	H
L	X	H	H	X	L	L
X	X	H	L	X	L	A_0
X	H	L	X	H	L	H
X	L	L	X	H	L	L
X	X	L	X	L	L	A_0
X	X	X	X	X	H	Z

A TO B ($\overline{OEA}$ = H)

INPUTS					OUTPUTS	
A	LEA1B	LEA2B	$\overline{OE1B}$	$\overline{OE2B}$	1B	2B
H	H	H	L	L	H	H
L	H	H	L	L	L	L
H	H	L	L	L	H	$2B_0$
L	H	L	L	L	L	$2B_0$
H	L	H	L	L	$1B_0$	H
L	L	H	L	L	$1B_0$	L
X	L	L	L	L	$1B_0$	$2B_0$
X	X	X	H	H	Z	Z
X	X	X	L	H	Active	Z
X	X	X	H	L	Z	Active
X	X	X	L	L	Active	Active

PRODUCT PREVIEW

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Output current in the low state, I_O: SN54ALVTH16260 . . . . . 96 mA
SN74ALVTH16260 . . . . . 128 mA
Output current in the high state, I_O: SN54ALVTH16260 . . . . . –48 mA
SN74ALVTH16260 . . . . . –64 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DGG package . . . . . 64°C/W
DGV package . . . . . 48°C/W
DL package . . . . . 56°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions, V_{CC} = 2.5 V ± 0.2 V (see Note 3)

			SN54ALVTH16260			SN74ALVTH16260			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		2.3		2.7	2.3		2.7	V
V_{IH}	High-level input voltage		1.7			1.7			V
V_{IL}	Low-level input voltage				0.7			0.7	V
V_I	Input voltage		0	V_{CC}	5.5	0	V_{CC}	5.5	V
I_{OH}	High-level output current				–6			–8	mA
I_{OL}	Low-level output current				6			8	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				18			24	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

PRODUCT PREVIEW

recommended operating conditions, V_{CC} = 3.3 V ± 0.3 V (see Note 3)

			SN54ALVTH16260			SN74ALVTH16260			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		3		3.6	3		3.6	V
V_{IH}	High-level input voltage		2			2			V
V_{IL}	Low-level input voltage				0.8			0.8	V
V_I	Input voltage		0	V_{CC}	5.5	0	V_{CC}	5.5	V
I_{OH}	High-level output current				–24			–32	mA
I_{OL}	Low-level output current				24			32	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				48			64	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH16260			SN74ALVTH16260			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.3 V to 2.7 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.3 V	I_{OH} = –6 mA	1.8						
			I_{OH} = –8 mA				1.8			
V_{OL}		V_{CC} = 2.3 V to 2.7 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 2.3 V	I_{OL} = 6 mA			0.4				
			I_{OL} = 8 mA						0.4	
			I_{OL} = 18 mA			0.5				
			I_{OL} = 24 mA						0.5	
I_I	Control inputs	V_{CC} = 2.7 V,	V_I = GND			±1			±1	µA
		V_{CC} = 0 or 2.7 V,	V_I = 2.7 V			1			1	
	A or B ports	V_{CC} = 2.7 V	V_I = V_{CC}			10			10	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}‡		V_{CC} = 2.3 V,	V_I = 0.7 V		115			115		µA
I_{BHH}§		V_{CC} = 2.3 V,	V_I = 1.7 V		–10			–10		µA
I_{BHLO}¶		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	300			300			µA
I_{BHHO}#		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	–300			–300			µA
I_{EX}‖		V_{CC} = 2.3 V,	V_O = 5.5 V						125	µA
$I_{OZ(PU/PD)}$☆		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 2.7 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.04	0.09		0.04	0.09	mA
			Outputs low		2.3	4.5		2.3	4.5	
			Outputs disabled		0.04	0.09		0.04	0.09	
C_i		V_{CC} = 2.5 V,	V_I = 2.5 V or 0							pF
C_{io}		V_{CC} = 2.5 V,	V_O = 2.5 V or 0							pF

† All typical values are at V_{CC} = 2.5 V, T_A = 25°C.
‡ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
§ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
¶ An external driver must source at least I_{BHLO} to switch this node from low to high.
# An external driver must sink at least I_{BHHO} to switch this node from high to low.
‖ Current into an output in the high state when V_O > V_{CC}
☆ High-impedance state during power up or power down

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH16260			SN74ALVTH16260			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 3 V to 3.6 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 3 V	I_{OL} = 16 mA						0.4	
			I_{OL} = 24 mA			0.5				
			I_{OL} = 32 mA						0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports	V_{CC} = 3.6 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			10			10	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}‡		V_{CC} = 3 V,	V_I = 0.8 V	75			75			µA
I_{BHH}§		V_{CC} = 3 V,	V_I = 2 V	–75			–75			µA
I_{BHLO}¶		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	500			500			µA
I_{BHHO}#		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	–500			–500			µA
I_{EX}‖		V_{CC} = 3 V,	V_O = 5.5 V			125			125	µA
$I_{OZ(PU/PD)}$☆		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.07	0.09		0.07	0.09	mA
			Outputs low		3.2	5		3.2	5	
			Outputs disabled		0.07	0.09		0.07	0.09	
ΔI_{CC}□		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.4			0.4	mA
C_i		V_{CC} = 3.3 V,	V_I = 3.3 V or 0							pF
C_{io}		V_{CC} = 3.3 V,	V_O = 3.3 V or 0							pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
§ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
¶ An external driver must source at least I_{BHLO} to switch this node from low to high.
# An external driver must sink at least I_{BHHO} to switch this node from high to low.
‖ Current into an output in the high state when V_O > V_{CC}
☆ High-impedance state during power up or power down
□ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

		SN54ALVTH16260		SN74ALVTH16260		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high					ns
t_{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B					ns
t_h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B					ns

timing requirements over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

		SN54ALVTH16260		SN74ALVTH16260		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high					ns
t_{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B					ns
t_h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B					ns

switching characteristics over recommended operating free-air temperature range, C_L = 30 pF, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16260		SN74ALVTH16260			UNIT
			MIN	MAX	MIN	TYP†	MAX	
t_{pd}	A or B	B or A						ns
	LE	A or B						
	SEL	A						
t_{en}	$\overline{OE}$	A or B						ns
t_{dis}	$\overline{OE}$	A or B						ns

† All typical values are at V_{CC} = 2.5 V, T_A = 25°C.

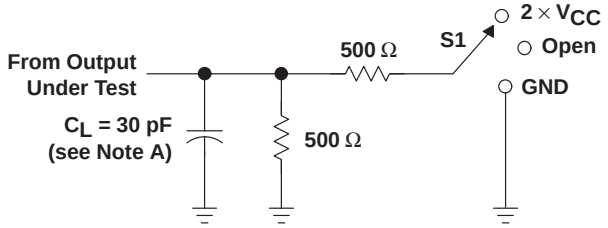
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16260		SN74ALVTH16260			UNIT
			MIN	MAX	MIN	TYP‡	MAX	
t_{pd}	A or B	B or A						ns
	LE	A or B						
	SEL	A						
t_{en}	$\overline{OE}$	A or B						ns
t_{dis}	$\overline{OE}$	A or B						ns

‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

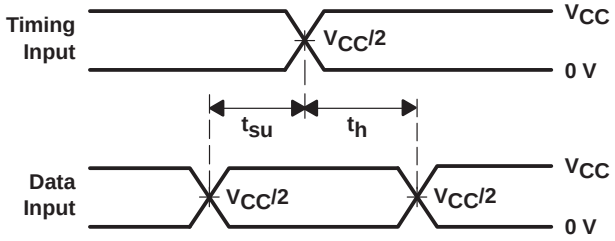
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

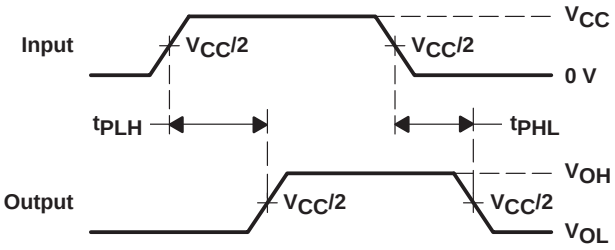


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

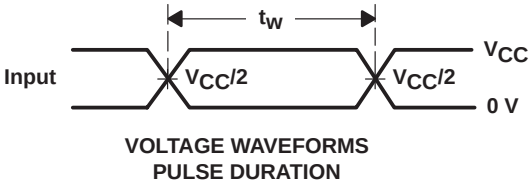
LOAD CIRCUIT



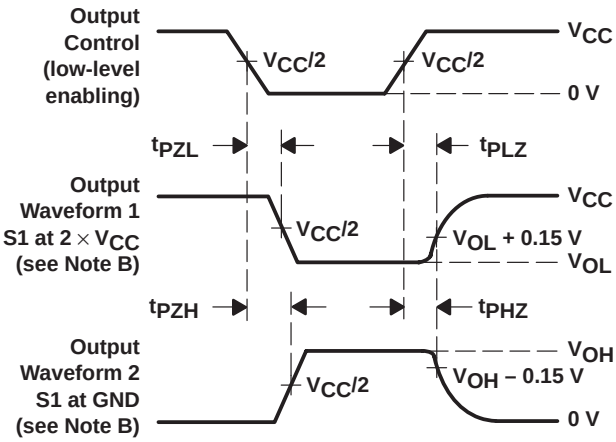
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

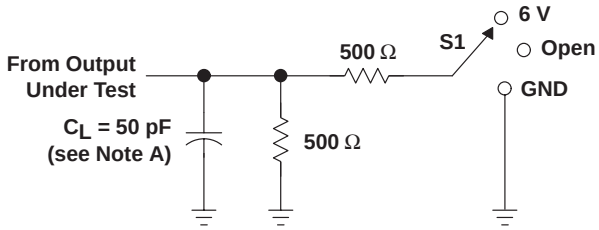


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

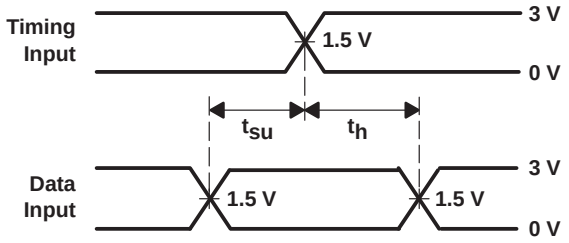
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 3.3 V ± 0.3 V

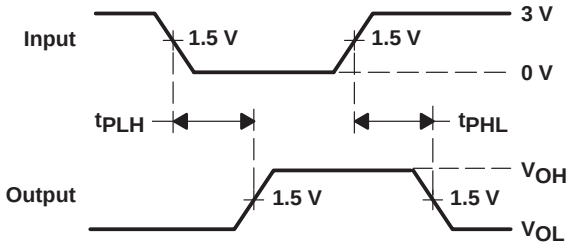


LOAD CIRCUIT

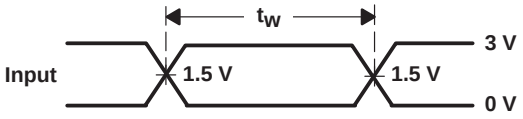
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



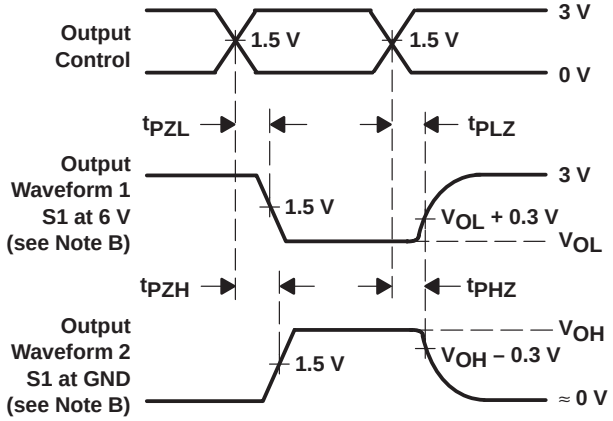
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

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